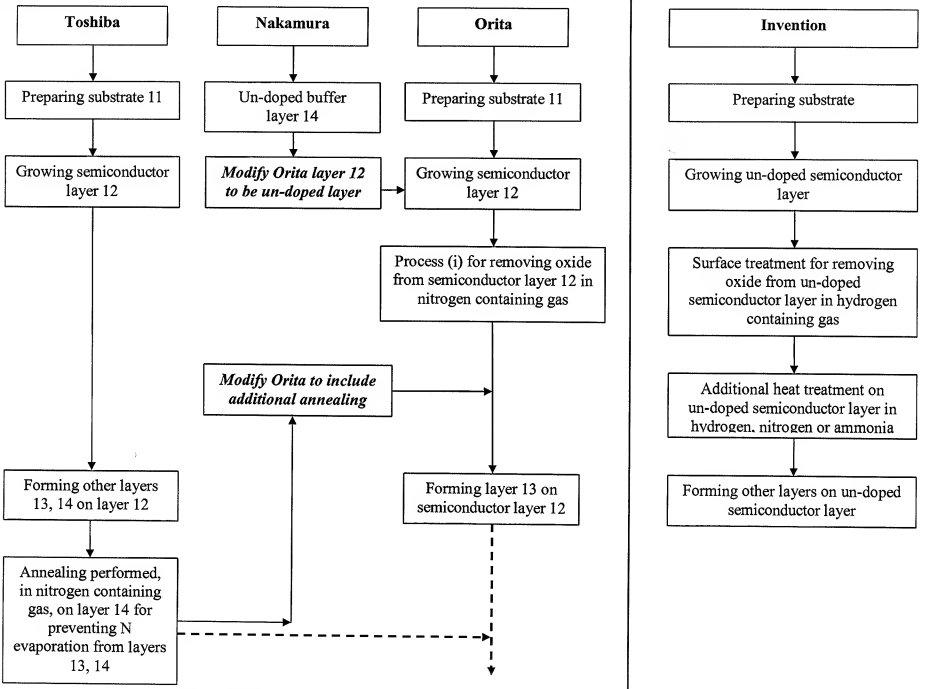
Toshiba
Preparing substrate 11
Growing semiconductor layer 12
Forming other layers 13, 14 on layer 12
Annealing performed, in nitrogen containing gas, on layer 14 for preventing N evaporation from layers 13, 14
Nakamura
Un-doped buffer layer 14
Modify Orita layer 12 to be un-doped layer
Modify Orita to include additional annealing
Orita
Preparing substrate 11
Growing semiconductor layer 12
Process (i) for removing oxide from semiconductor layer 12 in nitrogen containing gas
Forming layer 13 on semiconductor layer 12
Invention
Preparing substrate
Growing un-doped semiconductor layer
Surface treatment for removing oxide from un-doped semiconductor layer in hydrogen containing gas
Additional heat treatment on un-doped semiconductor layer in hydrogen, nitrogen or ammonia
Forming other layers on un-doped semiconductor layer

Exhibit A